

EP1100HSTTSC-12.352M



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 8 Pin DIP Metal Thru-Hole 12.352MHz ± 100 ppm - 20°C to +70°C

ELECTRICAL SPECIFICATIONS

Nominal Frequency	12.352MHz
Frequency Tolerance/Stability	± 100 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	-20°C to +70°C
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	45mA Maximum (Unloaded)
Output Voltage Logic High (Voh)	Vdd-0.4Vdc Minimum (IOH=-16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum (IOL=+16mA)
Rise/Fall Time	4nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 $\pm 5\%$ (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load)
Load Drive Capability	50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)
Pin 1 Input Voltage (Vih and Vil)	+2.0Vdc Minimum to enable output, +0.8Vdc Maximum to disable output, No Connect to enable output.
Disable Current	30mA Maximum (Pin 1 = Ground)
Standby Current	50 μ A Maximum (Pin 1 = Ground)
Peak to Peak Jitter (tPK)	100pSec Maximum, 50pSec Typical
RMS Period Jitter (tRMS)	13pSec Maximum, 8pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Lead Integrity	MIL-STD-883, Method 2004
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

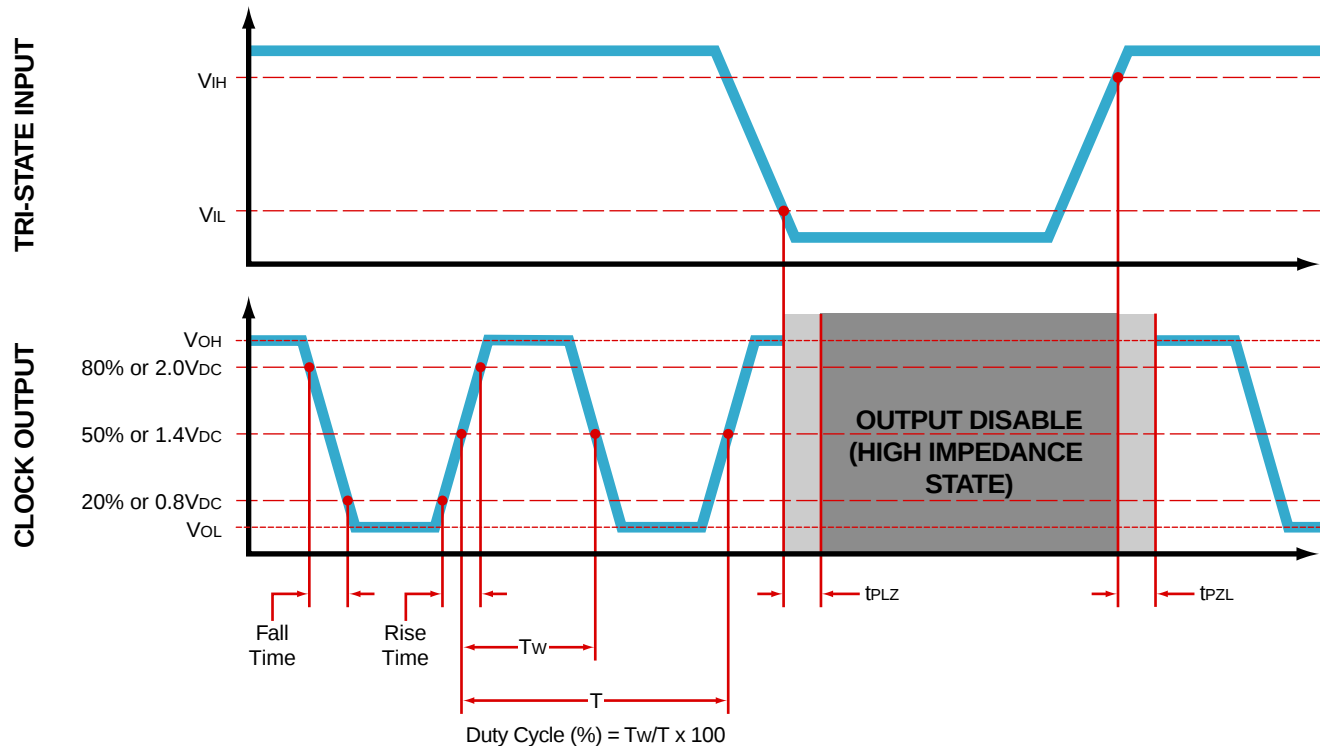
EP1100HSTTSC-12.352M

MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN CONNECTION	
1	Tri-State (High Impedance)
4	Case/Ground
5	Output
8	Supply Voltage

LINE MARKING	
1	ECLIPTEK
2	EP11TS EP11=Product Series
3	12.352M
4	XXYYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

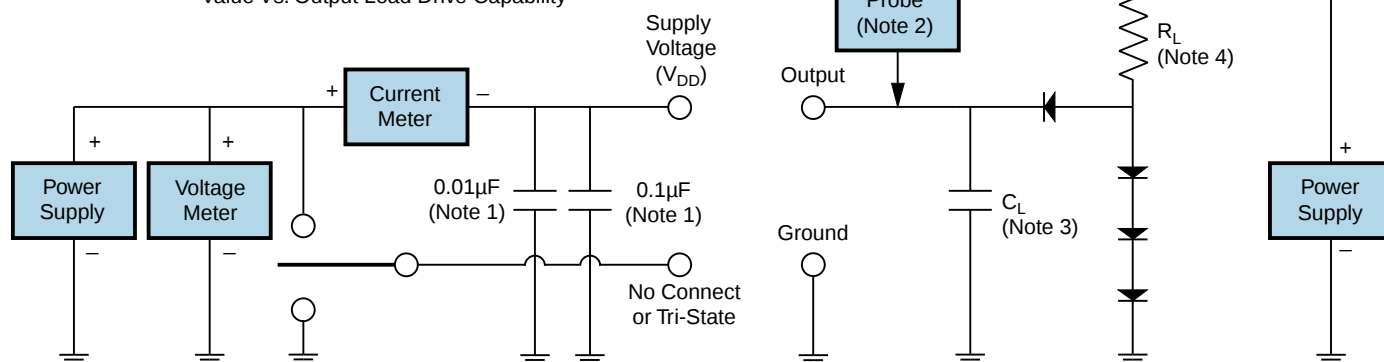
EP1100HSTTSC-12.352M **OUTPUT WAVEFORM & TIMING DIAGRAM**

EP1100HSTTSC-12.352M

Test Circuit for TTL Output

Output Load Drive Capability	R_L Value (Ohms)	C_L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.1 μ F low frequency tantalum bypass capacitor in parallel with a 0.01 μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MM74VHC00, MM74VHC14, or equivalent.

EP1100HSTTSC-12.352M **Test Circuit for CMOS Output**

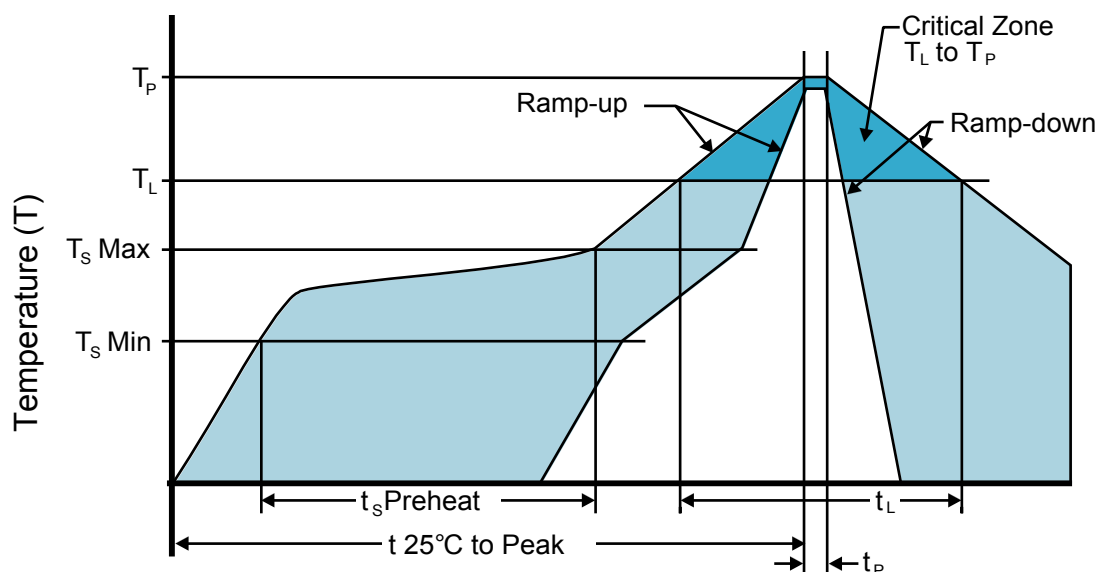
Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Solder Bath (Wave Solder)	Time (t)
--	----------

T_S MAX to T_L (Ramp-up Rate)	3°C/Second Maximum
Preheat	
- Temperature Minimum (T _S MIN)	150°C
- Temperature Typical (T _S TYP)	175°C
- Temperature Maximum (T _S MAX)	200°C
- Time (t _S MIN)	60 - 180 Seconds
Ramp-up Rate (T_L to T_P)	3°C/Second Maximum
Time Maintained Above:	
- Temperature (T _L)	217°C
- Time (t _L)	60 - 150 Seconds
Peak Temperature (T_P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T_P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t_p)	20 - 40 Seconds
Ramp-down Rate	6°C/Second Maximum
Time 25°C to Peak Temperature (t)	8 Minutes Maximum
Moisture Sensitivity Level	Level 1

EP1100HSTTSC-12.352M

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 185°C

T_s MAX to T_L (Ramp-up Rate) 5°C/Second Maximum

Preheat

- Temperature Minimum (T_s MIN) N/A
- Temperature Typical (T_s TYP) 150°C
- Temperature Maximum (T_s MAX) N/A
- Time (t_s MIN) 60 - 120 Seconds

Ramp-up Rate (T_L to T_P) 5°C/Second Maximum

Time Maintained Above:

- Temperature (T_L) 150°C
- Time (t_L) 200 Seconds Maximum

Peak Temperature (T_P) 185°C Maximum

Target Peak Temperature (T_P Target) 185°C Maximum 2 Times

Time within 5°C of actual peak (t_P) 10 Seconds Maximum 2 Times

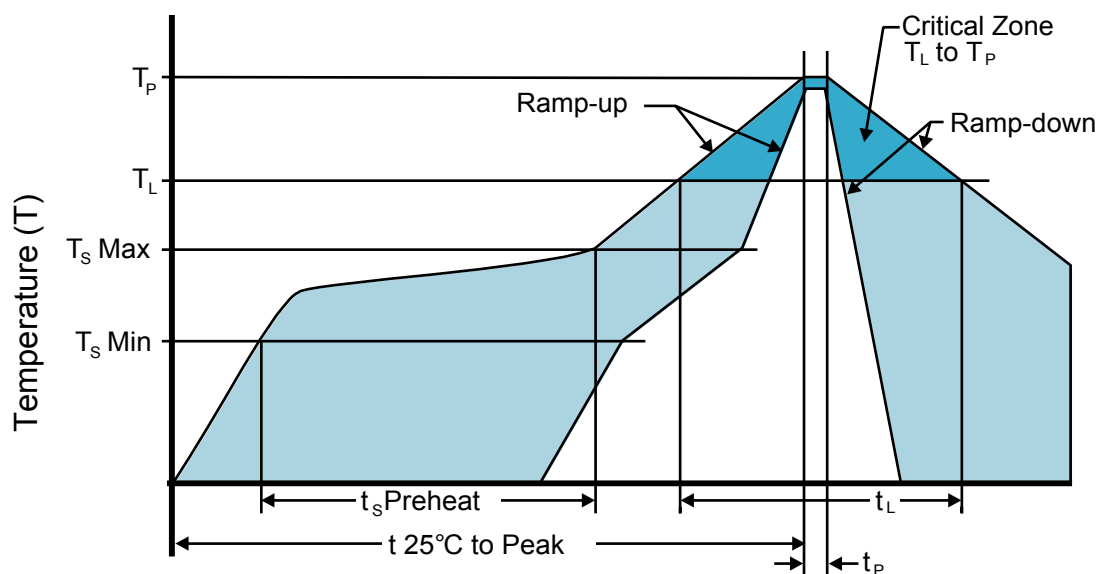
Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

EP1100HSTTSC-12.352M

Recommended Solder Reflow Methods



Low Temperature Solder Bath (Wave Solder) Time (t)

Ts MAX to Tl (Ramp-up Rate) 5°C/Second Maximum

Preheat

- Temperature Minimum (Ts MIN) N/A
- Temperature Typical (Ts TYP) 150°C
- Temperature Maximum (Ts MAX) N/A
- Time (ts MIN) 30 - 60 Seconds

Ramp-up Rate (Tl to Tp) 5°C/Second Maximum

Time Maintained Above:

- Temperature (Tl) 150°C
- Time (tL) 200 Seconds Maximum

Peak Temperature (Tp) 245°C Maximum

Target Peak Temperature (Tp Target) 245°C Maximum 1 Time / 235°C Maximum 2 Times

Time within 5°C of actual peak (tp) 5 Seconds Maximum 1 Time / 15 Seconds Maximum 2 Times

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum.